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TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

2SK246

FOR CONSTANT CURRENT, IMPEDANCE

Unit in mm

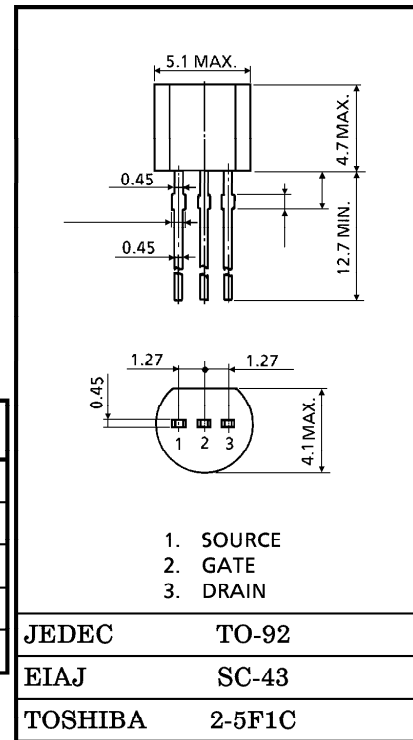
CONVERTER AND DC-AC HIGH INPUT

IMPEDANCE AMPLIFIER CIRCUIT APPLICATIONS

- High Breakdown Voltage : $V_{GDS} = -50V$
- High Input Impedance : $I_{GSS} = 1nA (Max.) (V_{GS} = -30V)$

MAXIMUM RATINGS ($T_a = 25^\circ C$)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|---------------------------|-----------|---------|------------|
| Gate-Drain Voltage | V_{GDS} | -50 | V |
| Gate Current | I_G | 10 | mA |
| Drain Power Dissipation | P_D | 300 | mW |
| Junction Temperature | T_j | 125 | $^\circ C$ |
| Storage Temperature Range | T_{stg} | -55~125 | $^\circ C$ |



Weight : 0.21g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|------------------------------|---------------------|--------------------------------------|------|------|------|------|
| Gate Cut-off Current | I_{GSS} | $V_{GS} = -30V, V_{DS} = 0$ | — | — | -1.0 | nA |
| Gate-Drain Breakdown Voltage | $V_{(BR) GDS}$ | $V_{DS} = 0, I_G = -100\mu A$ | -50 | — | — | V |
| Drain Current | I_{DSS} (Note) | $V_{DS} = 10V, V_{GS} = 0$ | 1.2 | — | 14 | mA |
| Gate-Source Cut-off Voltage | $V_{GS (OFF)}$ | $V_{DS} = 10V, I_D = 0.1\mu A$ | -0.7 | — | -6.0 | V |
| Forward Transfer Admittance | $ Y_{fs} $ | $V_{DS} = 10V, V_{GS} = 0, f = 1kHz$ | 1.5 | — | — | mS |
| Input Capacitance | C_{iss} | $V_{DS} = 10V, V_{GS} = 0, f = 1MHz$ | — | 9.0 | — | pF |
| Reverse Transfer Capacitance | C_{rss} | $V_{DG} = 10V, I_D = 0, f = 1MHz$ | — | 2.5 | — | pF |

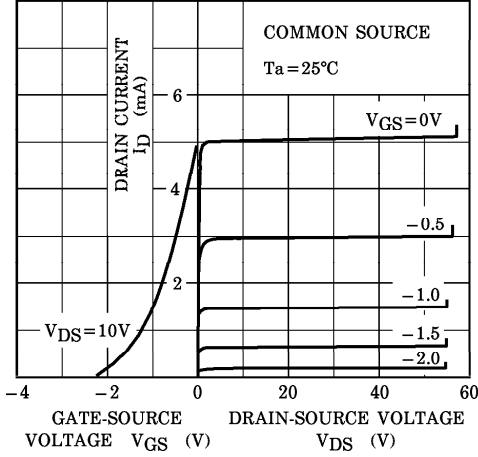
Note : I_{DSS} Classification Y : 1.2~3.0mA, GR : 2.6~6.5mA, BL : 6~14mA

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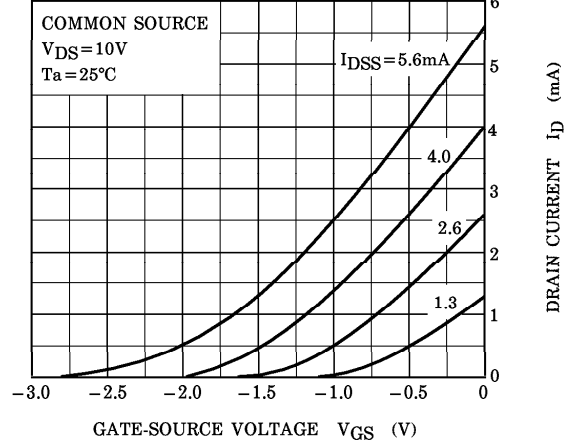
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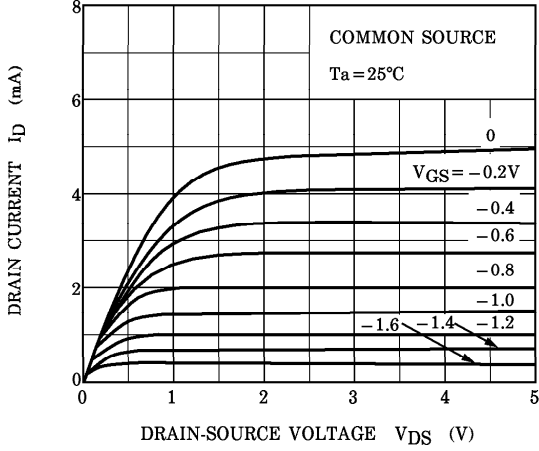
STATIC CHARACTERISTICS



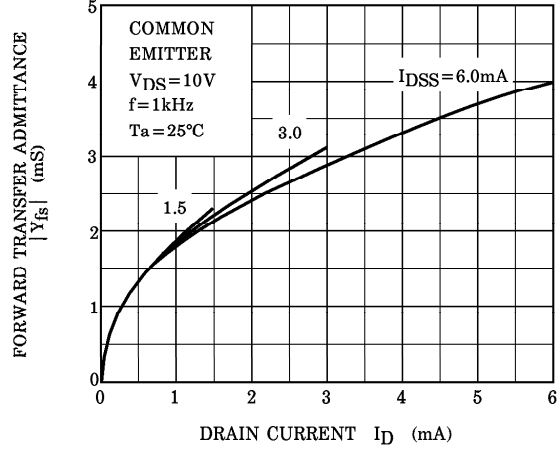
$I_D - V_{GS}$



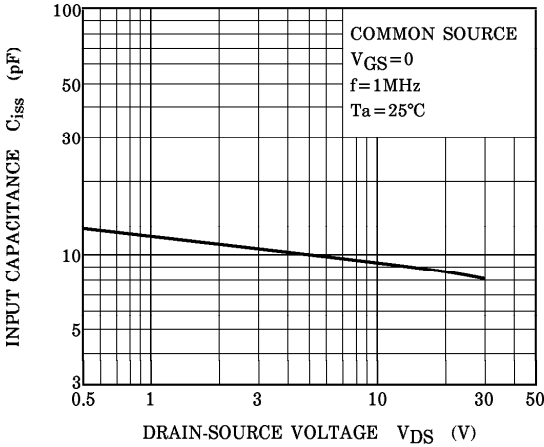
$I_D - V_{DS}$ (LOW VOLTAGE REGION)



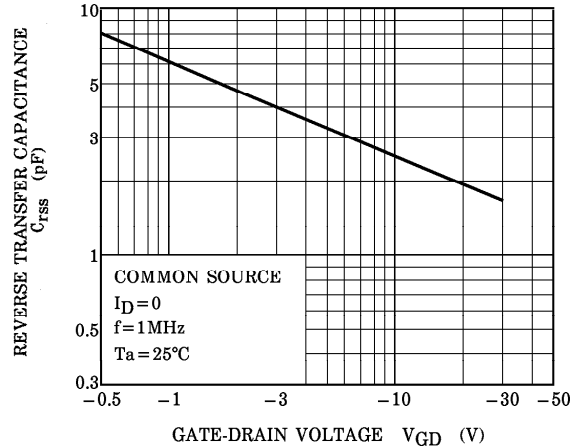
$|Y_{fs}| - I_D$



$C_{iss} - V_{DS}$



$C_{rss} - V_{GD}$



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